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APPLICANT: Luan C. Tran

FILING DATE
May 3, 2001

GROUP
2813

U.S. PATENT DOCUMENTS

*Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>LL</i>	AA	6,054,730	04/2000	Noguchi	257	306	
<i>LL</i>	AB	6,466,489	10/2002	leong et al.	365	189.09	
<i>LL</i>	AC	6,579,751	06/2003	Tran	438	194	
<i>LL</i>	AD	6,200,863	03/2001	Xiang et al.	438	286	
<i>LL</i>	AE	6,238,967	05/2001	Shiho et al.	438	244	
<i>LL</i>	AF	6,620,679	09/2003	Tzeng et al.	438	250	
<i>LL</i>	AG	6,008,080	12/1999	Chuang et al.	438	200	
<i>LL</i>	AH	5,834,851	11/1998	Ikeda et al.	257	903	
<i>LL</i>	AI	5,371,026	12/1994	Hayden et al.	437	41	
<i>LL</i>	AI	2003/0205745	11/2003	Nam	257	296	

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AJ							
	AK							
	AL							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

<i>LL</i>	AM	S. J. Ahn et al., "Novel DRAM Cell Transistor with Asymmetric Source and Drain Junction Profiles Improving
		Data Retention Characteristics" IEEE, 2002, pp. 176-177.
	AN	
	AO	

EXAMINER

DATE CONSIDERED

6/25/04

Schulte
*EXAMINER initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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